## MC74HCT132A

## Quad 2-Input NAND Gate with Schmitt-Trigger Inputs with LSTTL Compatible Inputs <br> High-Performance Silicon-Gate CMOS

The MC74HCT132A is identical in pinout to the LS132. The device inputs are compatible with standard CMOS outputs; with pull-up resistors, they are compatible with LSTTL outputs.

The MC74HCT132A can be used to enhance noise immunity or to square up slowly changing waveforms.

## Features

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: $1.0 \mu \mathrm{~A}$
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements as Defined by JEDEC Standard No. 7A
- Chip Complexity: 72 FETs or 18 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are $\mathrm{Pb}-$ Free, Halogen Free/BFR Free and are RoHS Compliant



## ON Semiconductor ${ }^{\circledR}$



FUNCTION TABLE

| Inputs |  | Output |
| :--- | :--- | :--- | :--- |
| $\mathbf{A}$ | B |  |
| L | L | H |
| L | H | H |
| H | L | H |
| H | H | L |

ORDERING INFORMATION
See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

Figure 1. Pin Assignment


Figure 2. Logic Diagram

ORDERING INFORMATION

| Device | Package | Shipping ${ }^{\dagger}$ |
| :---: | :---: | :---: |
| MC74HCT132ADG | SOIC-14 <br> (Pb-Free) | 55 Units / Rail |
| MC74HCT132ADR2G |  | 2500 / Tape \& Reel |
| NLV74HCT132ADR2G* |  | 2500 / Tape \& Reel |
| MC74HCT132ADTR2G | TSSOP-14 (Pb-Free) | 2500 / Tape \& Reel |
| NLVHCT132ADTR2G* |  | 2500 / Tape \& Reel |

$\dagger$ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

MC74HCT132A

MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
| :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{CC}}$ | Positive DC Supply Voltage | -0.5 to +7.0 | V |
| $\mathrm{V}_{\text {IN }}$ | Digital Input Voltage | -0.5 to +7.0 | V |
| $\mathrm{V}_{\text {OUT }}$ | DC Output Voltage $\begin{gathered}\text { Output in 3-State } \\ \text { High or Low State }\end{gathered}$ | $\begin{gathered} -0.5 \text { to }+7.0 \\ -0.5 \text { to } V_{C C} \quad+0.5 \end{gathered}$ | V |
| $\mathrm{I}_{\mathrm{K}}$ | Input Diode Current | -20 | mA |
| lok | Output Diode Current | $\pm 20$ | mA |
| Iout | DC Output Current, per Pin | $\pm 25$ | mA |
| $\mathrm{I}_{\mathrm{CC}}$ | DC Supply Current, $\mathrm{V}_{\text {CC }}$ and GND Pins | $\pm 75$ | mA |
| $\mathrm{I}_{\text {GND }}$ | DC Ground Current per Ground Pin | $\pm 75$ | mA |
| $\mathrm{T}_{\text {STG }}$ | Storage Temperature Range | -65 to +150 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\mathrm{L}}$ | Lead Temperature, 1 mm from Case for 10 Seconds | 260 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{J}$ | Junction Temperature Under Bias | + 150 | ${ }^{\circ} \mathrm{C}$ |
| $\theta_{\mathrm{JA}}$ | Thermal Resistance $r$ 14-SOIC | $\begin{aligned} & \hline 125 \\ & 170 \end{aligned}$ | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| $\mathrm{P}_{\mathrm{D}}$ | Power Dissipation in Still Air at $85^{\circ} \mathrm{C}$ SOIC | $\begin{aligned} & 500 \\ & 450 \end{aligned}$ | mW |
| MSL | Moisture Sensitivity | Level 1 |  |
| $\mathrm{F}_{\mathrm{R}}$ | Flammability Rating Oxygen Index: 30\% - 35\% | UL 94 V0 @ 0.125 in |  |
| $\mathrm{V}_{\text {ESD }}$ |  | $\begin{aligned} & >2000 \\ & >100 \\ & >500 \end{aligned}$ | V |
| ILatch-Up | Latch-Up Performance Above $\mathrm{V}_{\mathrm{CC}}$ and Below GND at $85^{\circ} \mathrm{C}$ (Note 4) | $\pm 300$ | mA |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Tested to EIA/JESD22-A114-A.
2. Tested to EIA/JESD22-A115-A.
3. Tested to JESD22-C101-A.
4. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter | Min | Max | Unit |
| :---: | :--- | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{CC}}$ | DC Supply Voltage (Referenced to GND) | 2.0 | 6.0 | V |
| $\mathrm{~V}_{\mathrm{IN}}, \mathrm{V}_{\text {OUT }}$ | DC Input Voltage, Output Voltage (Referenced to GND) | 0 | $\mathrm{~V}_{\mathrm{CC}}$ | V |
| $\mathrm{T}_{\mathrm{A}}$ | Operating Temperature, All Package Types | -55 | +125 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{t}_{\mathrm{r}} \mathrm{t}_{\mathrm{f}}$ | Input Rise and Fall Time (Figure 3) | - | No Limit <br> $($ Note 5$)$ | ns |

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.
5. When $\mathrm{V}_{\mathbb{I N}} \sim 0.5 \mathrm{~V}_{\mathrm{CC}}$, I $\mathrm{I}_{\mathrm{CC}} \gg$ quiescent current.
6. Unused inputs may not be left open. All inputs must be tied to a high-logic voltage level or a low-logic input voltage level.

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

| Symbol | Parameter | Test Conditions | $\begin{gathered} \hline \mathrm{v}_{\mathrm{cc}} \\ \mathrm{v} \end{gathered}$ | Guaranteed Limit |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | $-55^{\circ} \mathrm{C}$ to $25^{\circ} \mathrm{C}$ | $\leq 85{ }^{\circ} \mathrm{C}$ | $\leq 125^{\circ} \mathrm{C}$ |  |
| $\mathrm{V}_{\mathrm{T}_{+} \max }$ | Maximum Positive-Going Input Threshold Voltage | $\begin{aligned} & \mathrm{V}_{\text {OUT }}=0.1 \mathrm{~V} \\ & \text { \|lout } \end{aligned} \leq 20 \mu \mathrm{~A}$ | $\begin{aligned} & 4.5 \\ & 5.5 \end{aligned}$ | $\begin{aligned} & 1.9 \\ & 2.1 \end{aligned}$ | $\begin{aligned} & 1.9 \\ & 2.1 \end{aligned}$ | $\begin{aligned} & 1.9 \\ & 2.1 \end{aligned}$ | V |
| $\mathrm{V}_{\mathrm{T}_{+} \text {min }}$ | Minimum Positive-Going Input Threshold Voltage | $\begin{aligned} & \hline \mathrm{V}_{\text {OUT }}=0.1 \mathrm{~V} \\ & \mid \text { lout } \leq 20 \mu \mathrm{~A} \end{aligned}$ | $\begin{aligned} & 4.5 \\ & 5.5 \end{aligned}$ | $\begin{aligned} & 1.2 \\ & 1.4 \end{aligned}$ | $\begin{aligned} & 1.2 \\ & 1.4 \end{aligned}$ | $\begin{aligned} & 1.2 \\ & 1.4 \end{aligned}$ | V |
| $\mathrm{V}_{\text {T_max }}$ | Maximum Negative-Going Input Threshold Voltage | $\begin{aligned} & V_{\text {OUT }}=V_{\mathrm{CC}}-0.1 \mathrm{~V} \\ & \mid \text { lout } \leq 20 \mu \mathrm{~A} \end{aligned}$ | $\begin{aligned} & 4.5 \\ & 5.5 \end{aligned}$ | $\begin{aligned} & 1.2 \\ & 1.4 \end{aligned}$ | $\begin{aligned} & 1.2 \\ & 1.4 \end{aligned}$ | $\begin{aligned} & 1.2 \\ & 1.4 \end{aligned}$ | V |
| $\mathrm{V}_{\mathrm{T} \text { _min }}$ | Minimum Negative-Going Input Threshold Voltage | $\begin{aligned} & \mathrm{V}_{\text {OUT }}=\mathrm{V}_{\mathrm{CC}}-0.1 \mathrm{~V} \\ & \mid \text { lout } \leq 20 \mu \mathrm{~A} \end{aligned}$ | $\begin{aligned} & 4.5 \\ & 5.5 \end{aligned}$ | $\begin{aligned} & 0.5 \\ & 0.6 \end{aligned}$ | $\begin{aligned} & 0.5 \\ & 0.6 \end{aligned}$ | $\begin{aligned} & 0.5 \\ & 0.6 \end{aligned}$ | V |
| $\mathrm{V}_{\mathrm{H}}$ min (Note 7) | Minimum Hysteresis Voltage | $\begin{aligned} & \mathrm{V}_{\text {OUT }}=0.1 \mathrm{~V} \text { or } \mathrm{V}_{\mathrm{CC}}-0.1 \mathrm{~V} \\ & \text { \|lout } \leq 20 \mu \mathrm{~A} \end{aligned}$ | $\begin{aligned} & 4.5 \\ & 5.5 \end{aligned}$ | $\begin{aligned} & 0.4 \\ & 0.4 \end{aligned}$ | $\begin{aligned} & 0.4 \\ & 0.4 \end{aligned}$ | $\begin{aligned} & 0.4 \\ & 0.4 \end{aligned}$ | V |
| $\mathrm{V}_{\mathrm{OH}}$ | Minimum High-Level Output Voltage | $\begin{aligned} & \mathrm{V}_{\text {IN }} \leq \mathrm{V}_{\mathrm{T}_{-m i n}} \text { or } \mathrm{V}_{\mathrm{T}_{+} \max } \\ & \mid \mathrm{l}_{\mathrm{OUT}} \leq 20 \mu \mathrm{~A} \end{aligned}$ | $\begin{aligned} & 4.5 \\ & 5.5 \end{aligned}$ | $\begin{aligned} & 4.4 \\ & 5.4 \end{aligned}$ | $\begin{aligned} & 4.4 \\ & 5.4 \end{aligned}$ | $\begin{aligned} & 4.4 \\ & 5.4 \end{aligned}$ | V |
|  |  | $\begin{array}{\|c} \mathrm{V}_{\mathrm{IN}^{\prime}} \leq-\mathrm{V}_{\mathrm{T}_{-} \min \text { or }}^{\mathrm{V}_{\mathrm{T}_{+}} \max } \\ \left\|\mathrm{l}_{\mathrm{OUT}}\right\| \leq 4.0 \mathrm{~mA} \end{array}$ | 4.5 | 3.98 | 3.84 | 3.7 |  |
| $\mathrm{V}_{\text {OL }}$ | Maximum Low-Level Output Voltage | $\begin{aligned} & \mathrm{V}_{\text {IN }} \geq \mathrm{V}_{\mathrm{T}_{+}+\max } \\ & \mid \text { lout } \leq 20 \mu \mathrm{~A} \end{aligned}$ | $\begin{aligned} & 4.5 \\ & 5.5 \end{aligned}$ | $\begin{aligned} & \hline 0.1 \\ & 0.1 \end{aligned}$ | $\begin{aligned} & 0.1 \\ & 0.1 \end{aligned}$ | $\begin{aligned} & 0.1 \\ & 0.1 \end{aligned}$ | V |
|  |  | $\mathrm{V}_{\mathrm{IN}} \geq \mathrm{V}_{\mathrm{T}_{+}} \max \quad\left\|\mathrm{l}_{\text {OUT }}\right\| \leq 4.0 \mathrm{~mA}$ | 4.5 | 0.26 | 0.33 | 0.4 |  |
| $\mathrm{I}_{\mathrm{N}}$ | Maximum Input Leakage Current | $\mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\text {CC }}$ or GND | 5.5 | $\pm 0.1$ | $\pm 1.0$ | $\pm 1.0$ | $\mu \mathrm{A}$ |
| Icc | Maximum Quiescent Supply Current (per Package) | $\begin{aligned} & \mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{CC}} \text { or } \mathrm{GND} \\ & \mathrm{I}_{\text {OUT }}=0 \mu \mathrm{~A} \end{aligned}$ | 5.5 | 1.0 | 10 | 40 | $\mu \mathrm{A}$ |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
7. $\mathrm{V}_{\mathrm{H} \min }>\left(\mathrm{V}_{\mathrm{T}_{+} \min }\right)-\left(\mathrm{V}_{\mathrm{T}_{-} \max }\right) ; \mathrm{V}_{\mathrm{H}^{\max }}=\left(\mathrm{V}_{\mathrm{T}_{+}} \max \right)+\left(\mathrm{V}_{\mathrm{T}_{-}} \min \right)$.

AC ELECTRICAL CHARACTERISTICS ( $\mathrm{C}_{\mathrm{L}}=50 \mathrm{pF}$, $\operatorname{Input} \mathrm{t}_{\mathrm{r}}=\mathrm{t}_{\mathrm{f}}=6.0 \mathrm{~ns}, \mathrm{~V}_{\mathrm{CC}}=5.0 \mathrm{~V} \pm 10 \%$ )

| Symbol | Parameter | $\begin{gathered} \mathrm{v}_{\mathrm{CC}} \\ \mathrm{v} \end{gathered}$ | Guaranteed Limit |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  | $-55^{\circ} \mathrm{C}$ to $25^{\circ} \mathrm{C}$ | $\leq 85^{\circ} \mathrm{C}$ | $\leq 125^{\circ} \mathrm{C}$ |  |
| $t_{\text {PLH }}$, <br> $t_{\text {PHL }}$ | Maximum Propagation Delay, Input A or B to Output Y (Figures 3 and 4) | 5.0 | 25 | 31 | 38 | ns |
| $\begin{aligned} & \mathrm{t}_{\mathrm{T} \mathrm{LH}}, \\ & \mathrm{t}_{\mathrm{TH}} \mathrm{HL} \end{aligned}$ | Maximum Output Transition Time, Any Output (Figures 3 and 4) | 5.0 | 15 | 19 | 22 | ns |
| $\mathrm{C}_{\text {in }}$ | Maximum Input Capacitance | - | 10 | 10 | 10 | pF |


|  |  | Typical @ 25 ${ }^{\circ} \mathbf{C}, \mathbf{V}_{\mathbf{C C}}=\mathbf{5 . 0} \mathbf{V}$ |  |
| :--- | :--- | :---: | :---: |
| $\mathrm{C}_{\text {PD }}$ | Power Dissipation Capacitance (per Gate) (Note 8) | 24 | pF |

8. Used to determine the no-load dynamic power consumption: $P_{D}=C_{P D} V_{C C}^{2 f}+I_{C C} V_{C C}$.

$\mathrm{V}_{\mathrm{I}}=$ GND to 3.0 V
$V_{1}=$ GND to
$V_{M}=1.3 \mathrm{~V}$
Figure 3. Switching Waveforms

*Includes all probe and jig capacitance

Figure 4. Test Circuit


Figure 5. Typical Schmitt-Trigger Applications


SOIC-14 NB
CASE 751A-03
ISSUE L
SCALE 1:1


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b DOES NOT INCLUDE DAMBAR

PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE

MOLD PROTRUSIONS.
5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

| DIM | MILLIMETERS |  | INCHES |  |
| :---: | :---: | :---: | :---: | :---: |
|  | MIN | MAX | MIN | MAX |
|  | 1.35 | 1.75 | 0.054 | 0.068 |
| A1 | 0.10 | 0.25 | 0.004 | 0.010 |
| A3 | 0.19 | 0.25 | 0.008 | 0.010 |
| b | 0.35 | 0.49 | 0.014 | 0.019 |
| D | 8.55 | 8.75 | 0.337 | 0.344 |
| E | 3.80 | 4.00 | 0.150 | 0.157 |
| e | 1.27 | BSC | 0.050 | BSC |
| H | 5.80 | 6.20 | 0.228 | 0.244 |
| h | 0.25 | 0.50 | 0.010 | 0.019 |
| L | 0.40 | 1.25 | 0.016 | 0.049 |
| M | $0^{\circ}$ | $7^{\circ}$ | $0^{\circ}$ | $7^{\circ}$ |

## SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS
*For additional information on our $\mathrm{Pb}-$ Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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STYLE 1:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. NO CONNECTION
5. ANODE/CATHODE
6. NO CONNECTION
7. ANODE/CATHODE
8. ANODE/CATHODE
9. ANODE/CATHODE
10. NO CONNECTION
11. ANODE/CATHODE
12. ANODE/CATHODE
13. NO CONNECTION
4. COMMON ANODE
STYLE $5:$

PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHOD
4. ANODE/CATHOD
4. ANODE/CATHODE
5. ANODE/CATHODE
6. NO CONNECTION
7. COMMON ANODE
8. COMMON CATHOD
9. ANODE/CATHODE
10. ANODE/CATHODE
11. ANODE/CATHODE
12. ANODE/CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 2 :
CANCELLED

STYLE 3:
PIN 1. NO CONNECTION 2. ANODE 3. ANODE
4. NO CONNECTION 5. ANODE
6. NO CONNECTION
7. ANODE
8. ANODE
9. ANODE
10. NO CONNECTION
11. ANODE
12. ANODE
13. NO CONNECTION
14. COMMON CATHODE

## STYLE 6

PIN 1. CATHODE
2. CATHODE
3. CATHODE
4. CATHODE
5. CATHODE
5. CATHODE
6. CATHODE
7. CATHOD
8. ANODE
10. ANODE
11. ANODE
12. ANODE
13. ANODE
14. ANODE

STYLE 7:
PIN 1. ANODE/CATHODE
2. COMMON ANODE
3. COMMON CATHODE
4. ANODE/CATHODE
4. ANODE/CATHODE
5. ANODE/CATHODE
6. ANODE/CATHODE
7. ANODE/CATHODE
8. ANODE/CATHODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. COMMON CATHODE
11. COMMON CATHOD
13. ANODE/CATHODE
14. ANODE/CATHODE

STYLE 4:
PIN 1. NO CONNECTION 2. CATHODE
3. CATHODE
4. NO CONNECTION
5. CATHODE
6. NO CONNECTION
7. CATHODE
. CATHODE
9. CATHODE
10. NO CONNECTION
11. CATHODE
12. CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 8:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. NO CONNECTION
4. NO CONNECTION
5. ANODE/CATHODE
6. ANODE/CATHODE
7. COMMON ANODE
8. COMMON ANODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. NO CONNECTION
11. NO CONNECTION
12. ANODE/CATHODE
12. ANODE/CATHODE
13. ANODE/CATHODE
13. ANODE/CATHODE
14. COMMON CATHODE

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NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS MOLD FLASH OR GATE BURRS SHALL NOT MOLD FLASH OR GATE BURRS
4. DIMENSION B DOES NOT INCLUDE

INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR
PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

| DIM | MILLIMETERS |  | INCHES |  |
| :---: | :---: | :---: | :---: | :---: |
|  | MIN | MAX | MIN | MAX |
| A | 4.90 | 5.10 | 0.193 | 0.200 |
| B | 4.30 | 4.50 | 0.169 | 0.177 |
| C | --- | 1.20 | --- | 0.047 |
| D | 0.05 | 0.15 | 0.002 | 0.006 |
| F | 0.50 | 0.75 | 0.020 | 0.030 |
| G | 0.65 | BSC | 0.026 |  |
| BSC |  |  |  |  |
| H | 0.50 | 0.60 | 0.020 | 0.024 |
| J | 0.09 | 0.20 | 0.004 | 0.008 |
| J1 | 0.09 | 0.16 | 0.004 | 0.006 |
| K | 0.19 | 0.30 | 0.007 | 0.012 |
| K1 | 0.19 | 0.25 | 0.007 | 0.010 |
| L | 6.40 | BSC | 0.252 | BSC |
| M | $0{ }^{\circ}$ | $8^{\circ}$ | $0^{\circ}$ | $8^{\circ}$ |

GENERIC MARKING DIAGRAM*



| A | $=$ Assembly Location |
| :--- | :--- |
| L | $=$ Wafer Lot |
| Y | $=$ Year |
| W | $=$ Work Week |
| - | $=$ Pb-Free Package |

(Note: Microdot may be in either location)
*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " $\bullet$ ", may or may not be present.

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| ---: | :--- | :--- | :--- |
| DESCRIPTION: | TSSOP-14 WB | PAGE 1 OF 1 |

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